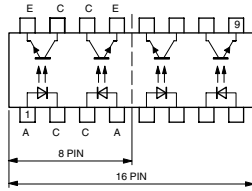
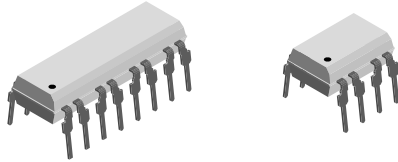


Optocoupler, Phototransistor Output, Multichannel



17188


FEATURES

- CNY74-2H includes 2 isolator channels
- CNY74-4H includes 4 isolator channels
- Isolation test voltage $V_{ISO} = 5000 V_{RMS}$
- Test class 25/100/21 DIN 40 045
- Low coupling capacitance of typical 0.3 pF
- Current transfer ratio (CTR) of typical 100 %
- Low temperature coefficient of CTR
- Wide ambient temperature range
- Coupling system U
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC


**RoHS
COMPLIANT**
DESCRIPTION

The CNY74-2H and CNY74-4H consist of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in an 8-pin, resp. 16-pin plastic dual inline package.

The elements are mounted on one leadframe providing a fixed distance between input and output for highest safety requirements.

APPLICATIONS

- Galvanically separated circuits, non-interacting switches

AGENCY APPROVALS

- UL1577, file no. E76222 system code U, double protection
- CSA22.2 bulletin 5A

ORDER INFORMATION

PART	REMARKS
CNY74-2H	CTR 50 to 600 %, DIP-8
CNY74-4H	CTR 50 to 600 %, DIP-16

Note

CNY74-2H and CNY74-4M are marked as CNY74-2 and CNY74-4 respectively.

ABSOLUTE MAXIMUM RATINGS (1)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10 \mu s$	I_{FSM}	1.5	A
Power dissipation		P_{diss}	100	mW
Junction temperature		T_j	125	°C
OUTPUT				
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10 ms$	I_{CM}	100	mA
Power dissipation		P_{diss}	150	mW
Junction temperature		T_j	125	°C

ABSOLUTE MAXIMUM RATINGS (1)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
COUPLER				
AC isolation test voltage (RMS)	t = 1 min	$V_{ISO}^{(2)}$	5000	V_{RMS}
Total power dissipation		P_{tot}	250	mW
Ambient temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 55 to + 125	°C
Soldering temperature	2 mm from case, t ≤ 10 s	T_{slid}	260	°C

Notes

(1) $T_{amb} = 25\text{ °C}$, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Related to standard climate 23/50 DIN 50014.

(3) Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS (1)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	$I_F = 50\text{ mA}$	V_F		1.25	1.6	V
OUTPUT						
Collector emitter voltage	$I_C = 1\text{ mA}$	V_{CEO}	70			V
Emitter collector voltage	$I_E = 100\text{ }\mu\text{A}$	V_{ECO}	7			V
Collector dark current	$V_{CE} = 20\text{ V}$, $I_F = 0\text{ A}$, $E = 0$	I_{CEO}			100	nA
COUPLER						
DC isolation test voltage	t = 2 s	$V_{ISO}^{(2)}$	5000			V
Isolation resistance	$V_{IO} = 1000\text{ V}$, 40 % relative humidity	$R_{IO}^{(2)}$		10^{12}		Ω
Collector emitter saturation voltage	$I_F = 10\text{ mA}$, $I_C = 1\text{ mA}$	V_{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 100\text{ }\Omega$	f_c		100		kHz
Coupling capacitance	f = 1 MHz	C_k		0.3		pF

Note

(1) $T_{amb} = 25\text{ °C}$, unless otherwise specified. Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

(2) Related to standard climate 23/50 DIN 50014.

CURRENT TRANSFER RATIO						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$V_{CE} = 5\text{ V}$, $I_F = 5\text{ mA}$	CTR	50	100	600	%
	$V_{CE} = 5\text{ V}$, $I_F = 10\text{ mA}$	CTR	60	120		%

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Delay time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$ (see figure 1)	t_d		3.0		μs
Rise time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$ (see figure 1)	t_r		3.0		μs
Fall time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$ (see figure 1)	t_f		4.7		μs
Storage time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$ (see figure 1)	t_s		0.3		μs
Turn-on time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$ (see figure 1)	t_{on}		6.0		μs
Turn-off time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\text{ }\Omega$ (see figure 1)	t_{off}		5.0		μs
Turn-on time	$V_S = 5\text{ V}$, $I_C = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$ (see figure 2)	t_{on}		9.0		μs
Turn-off time	$V_S = 5\text{ V}$, $I_C = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$ (see figure 2)	t_{off}		18.0		μs

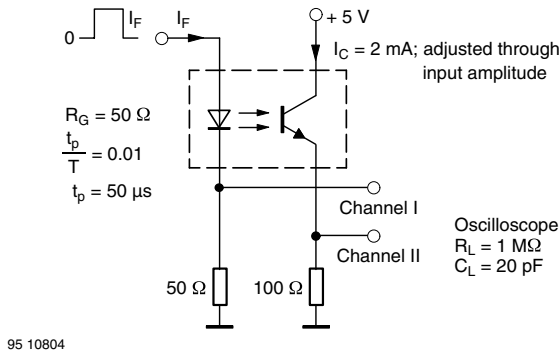


Fig. 1 - Test Circuit, Non-Saturated Operation

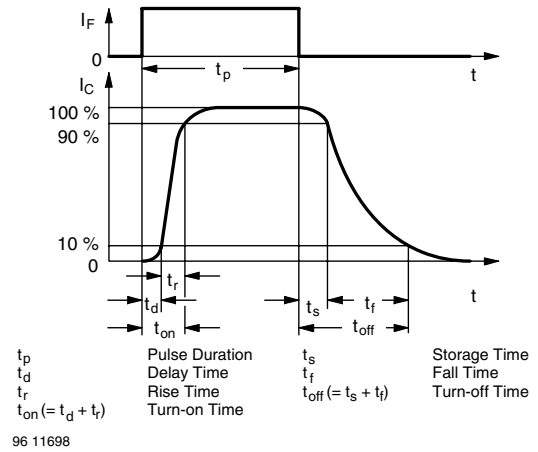


Fig. 3 - Switching Times

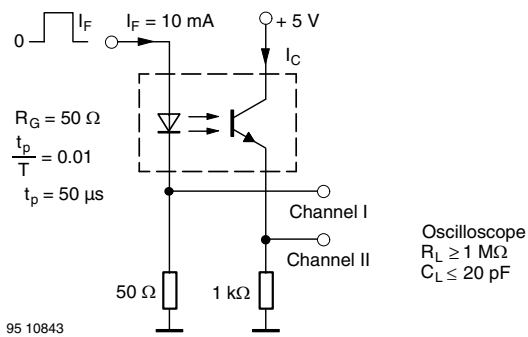


Fig. 2 - Test Circuit, Saturated Operation

TYPICAL CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

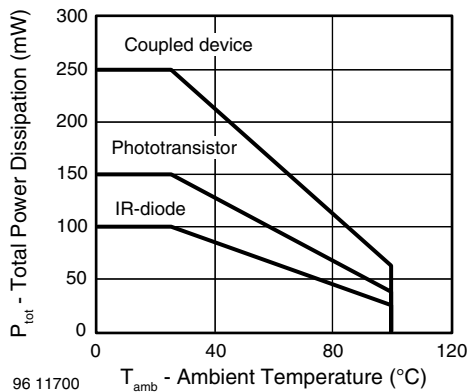


Fig. 4 - Total Power Dissipation vs. Ambient Temperature

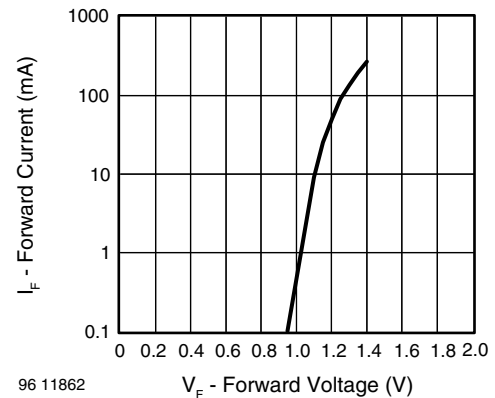


Fig. 5 - Forward Current vs. Forward Voltage

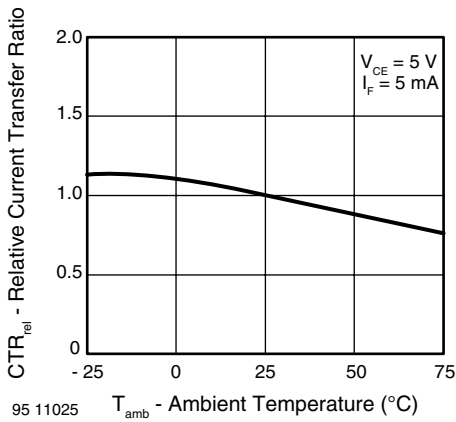


Fig. 6 - Relative Current Transfer Ratio vs. Ambient Temperature

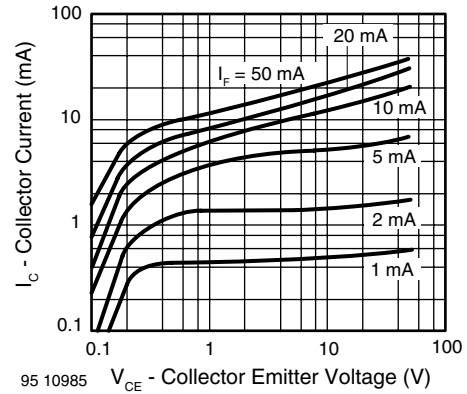


Fig. 9 - Collector Current vs. Collector Emitter Voltage

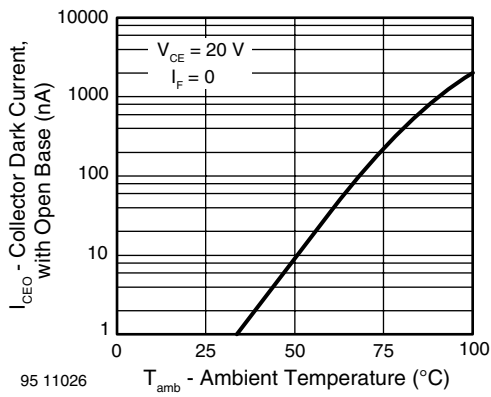


Fig. 7 - Collector Dark Current vs. Ambient Temperature

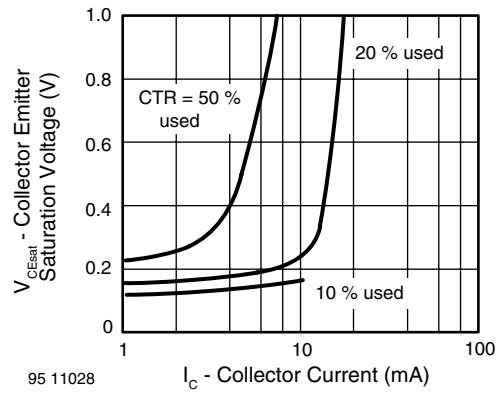


Fig. 10 - Collector Emitter Saturation Voltage vs. Collector Current

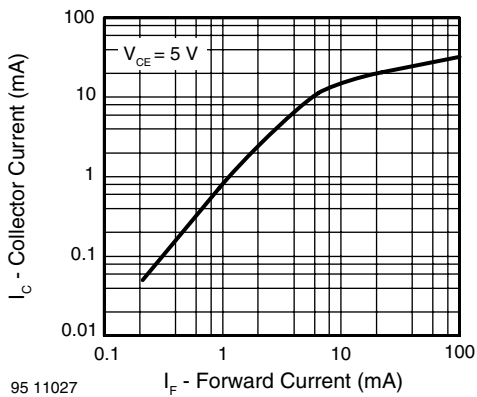


Fig. 8 - Collector Current vs. Forward Current

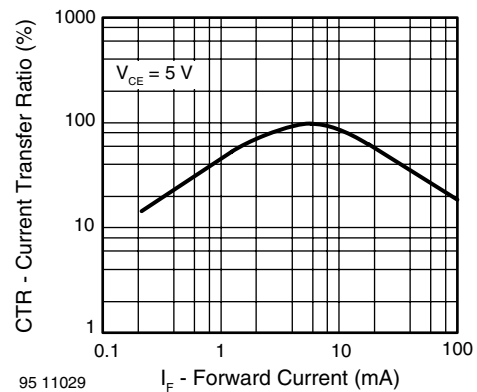
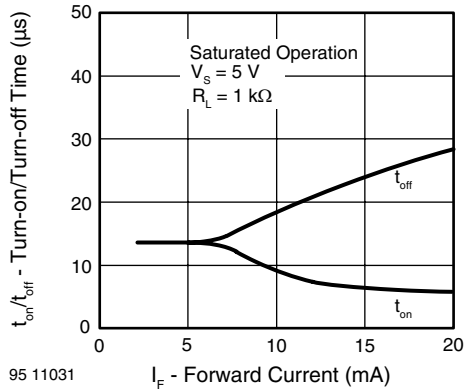


Fig. 11 - Current Transfer Ratio vs. Forward Current



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Fig. 12 - Turn-on/off Time vs. Forward Current

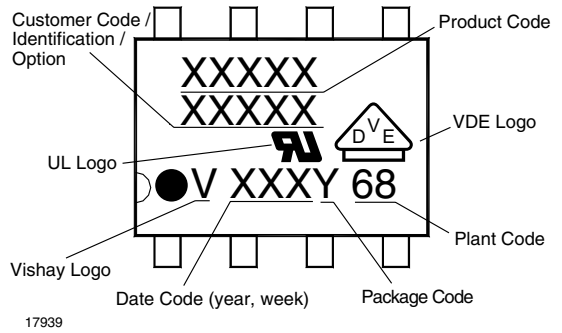
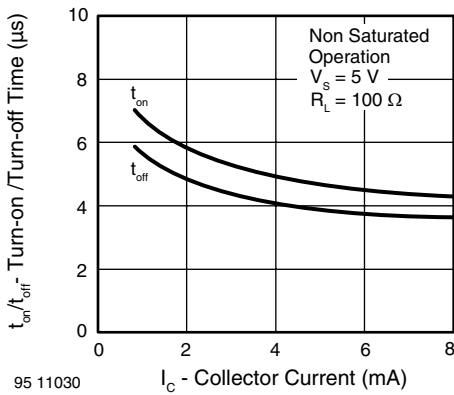


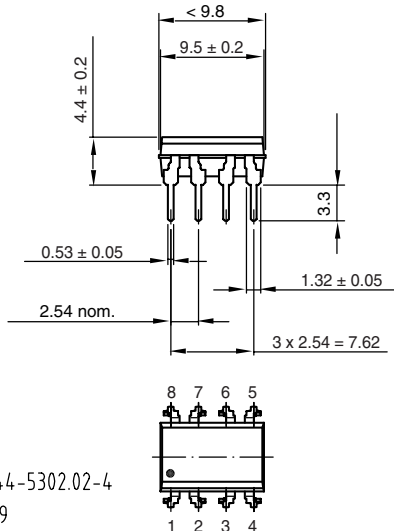
Fig. 14 - Marking Example



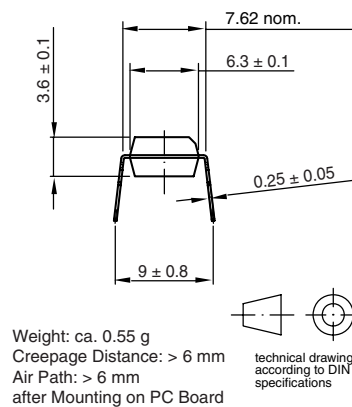
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Fig. 13 - Turn-on/off Time vs. Collector Current

PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5302.02-4
Issue: 4; 02.06.99



Weight: ca. 0.55 g
Creepage Distance: > 6 mm
Air Path: > 6 mm
after Mounting on PC Board

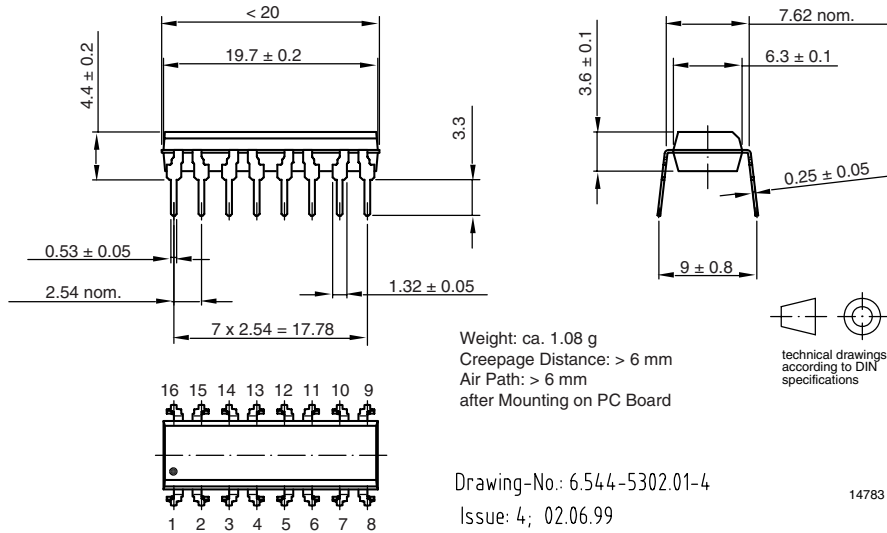
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CNY74-2H/CNY74-4H



Vishay Semiconductors Optocoupler, Phototransistor Output,
Multichannel

PACKAGE DIMENSIONS in millimeters



**OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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